

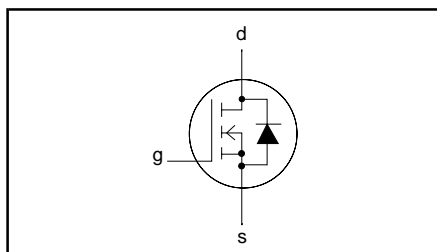
# N-channel TrenchMOS™ transistor Logic level FET

## PHB11N03LT, PHD11N03LT

### FEATURES

- 'Trench' technology
- Low on-state resistance
- Fast switching
- Logic level compatible

### SYMBOL



### QUICK REFERENCE DATA

$V_{DSS} = 30\text{ V}$
$I_D = 10.5\text{ A}$
$R_{DS(ON)} \leq 150\text{ m}\Omega$ ( $V_{GS} = 5\text{ V}$ )
$R_{DS(ON)} \leq 130\text{ m}\Omega$ ( $V_{GS} = 10\text{ V}$ )

### GENERAL DESCRIPTION

N-channel enhancement mode, logic level, field-effect power transistor in a plastic envelope using 'trench' technology.

#### Applications:-

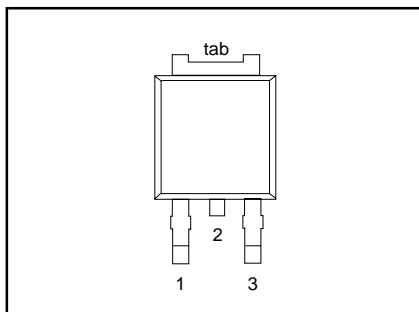
- d.c. to d.c. converters
- switched mode power supplies

The PHB11N03LT is supplied in the SOT404 (D<sup>2</sup>PAK) surface mounting package.  
The PHD11N03LT is supplied in the SOT428 (DPAK) surface mounting package.

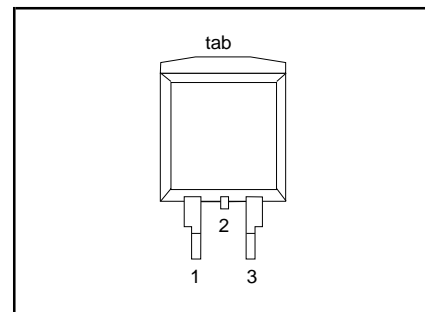
### PINNING

PIN	DESCRIPTION
1	gate
2	drain <sup>1</sup>
3	source
tab	drain

#### SOT428 (DPAK)



#### SOT404 (D<sup>2</sup>PAK)



### LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134)

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$V_{DSS}$	Drain-source voltage	$T_j = 25\text{ }^\circ\text{C}$ to $175\text{ }^\circ\text{C}$	-	30	V
$V_{DGR}$	Drain-gate voltage	$T_j = 25\text{ }^\circ\text{C}$ to $175\text{ }^\circ\text{C}$ ; $R_{GS} = 20\text{ k}\Omega$	-	30	V
$V_{GS}$	Gate-source voltage		-	$\pm 15$	V
$V_{GSM}$	Pulsed gate-source voltage		-	$\pm 20$	V
$I_D$	Continuous drain current	$T_{mb} = 25\text{ }^\circ\text{C}$	-	10.3	A
		$T_{mb} = 100\text{ }^\circ\text{C}$	-	7.3	A
$I_{DM}$	Pulsed drain current	$T_{mb} = 25\text{ }^\circ\text{C}$	-	41	A
$P_D$	Total power dissipation	$T_{mb} = 25\text{ }^\circ\text{C}$	-	33	W
$T_j, T_{stg}$	Operating junction and storage temperature		-55	175	$^\circ\text{C}$

<sup>1</sup> It is not possible to make contact to pin 2 of the SOT404 or SOT428 package

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### AVALANCHE ENERGY LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134)

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$E_{AS}$	Non-repetitive avalanche energy	Unclamped inductive load, $I_{AS} = 3.3$ A; $t_p = 220$ $\mu$ s; $T_j$ prior to avalanche = 25°C; $V_{DD} \leq 15$ V; $R_{GS} = 50$ $\Omega$ ; $V_{GS} = 5$ V; refer to fig:15	-	25	mJ
$I_{AS}$	Peak non-repetitive avalanche current		-	10.3	A

### THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
$R_{th\ j-mb}$	Thermal resistance junction to mounting base	SOT428 and SOT404 package, pcb mounted, minimum footprint	-	4.5	K/W
$R_{th\ j-a}$	Thermal resistance junction to ambient		50	-	K/W

### ELECTRICAL CHARACTERISTICS

 $T_j = 25^\circ\text{C}$  unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$V_{(BR)DSS}$	Drain-source breakdown voltage	$V_{GS} = 0$ V; $I_D = 0.25$ mA; $T_j = -55^\circ\text{C}$	30 26	- -	- -	V V
$V_{GS(TO)}$	Gate threshold voltage	$V_{DS} = V_{GS}$ ; $I_D = 1$ mA $T_j = 175^\circ\text{C}$ $T_j = -55^\circ\text{C}$	1.0 0.5 -	1.5 - -	2.0 - 2.3	V V V
$R_{DS(ON)}$	Drain-source on-state resistance	$V_{GS} = 10$ V; $I_D = 5.5$ A $V_{GS} = 5$ V; $I_D = 5.5$ A $T_j = 175^\circ\text{C}$	- - -	100 120 250	130 150 315	m $\Omega$ m $\Omega$ m $\Omega$
$g_{fs}$	Forward transconductance	$V_{DS} = 25$ V; $I_D = 5.5$ A $T_j = 175^\circ\text{C}$	4	7	-	S
$I_{GSS}$	Gate source leakage current	$V_{GS} = \pm 5$ V; $V_{DS} = 0$ V	-	10	100	nA
$I_{DSS}$	Zero gate voltage drain current	$V_{DS} = 30$ V; $V_{GS} = 0$ V; $T_j = 175^\circ\text{C}$	-	0.05	10 500	$\mu$ A $\mu$ A
$Q_{g(tot)}$	Total gate charge	$I_D = 10$ A; $V_{DD} = 15$ V; $V_{GS} = 5$ V	-	3.8	-	nC
$Q_{gs}$	Gate-source charge		-	1.2	-	nC
$Q_{gd}$	Gate-drain (Miller) charge		-	1.7	-	nC
$t_{d\ on}$	Turn-on delay time	$V_{DD} = 30$ V; $R_D = 2.7$ $\Omega$ ; $R_G = 10$ $\Omega$ ; $V_{GS} = 5$ V Resistive load	-	6	16	ns
$t_r$	Turn-on rise time		-	64	80	ns
$t_{d\ off}$	Turn-off delay time		-	20	30	ns
$t_f$	Turn-off fall time		-	26	40	ns
$L_d$	Internal drain inductance	Measured from tab to centre of die	-	3.5	-	nH
$L_d$	Internal drain inductance	Measured from drain lead to centre of die (SOT78 package only)	-	4.5	-	nH
$L_s$	Internal source inductance	Measured from source lead to source bond pad	-	7.5	-	nH
$C_{iss}$	Input capacitance	$V_{GS} = 0$ V; $V_{DS} = 25$ V; $f = 1$ MHz	-	250	330	pF
$C_{oss}$	Output capacitance		-	55	75	pF
$C_{rss}$	Feedback capacitance		-	42	55	pF

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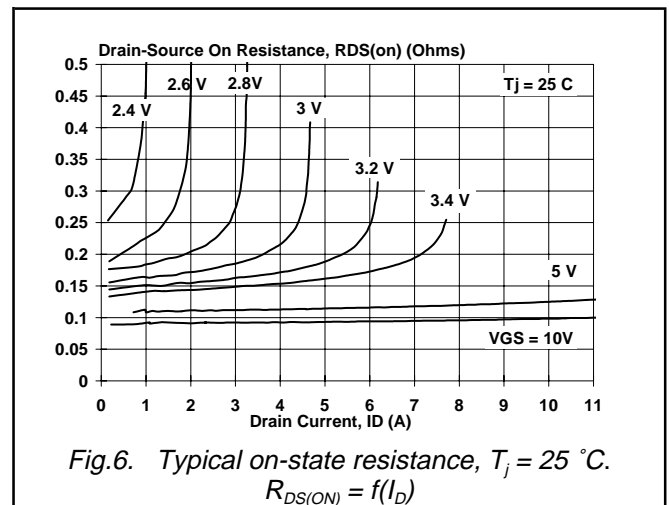
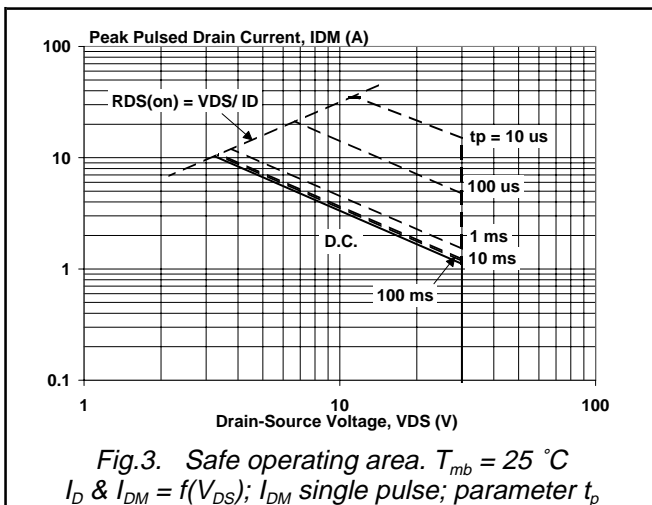
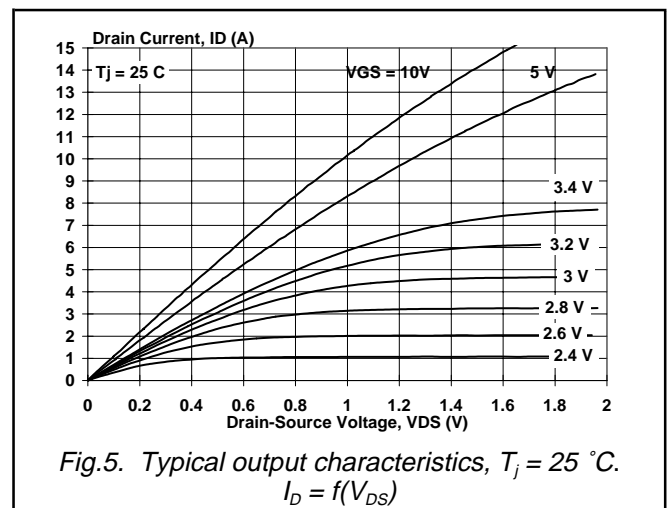
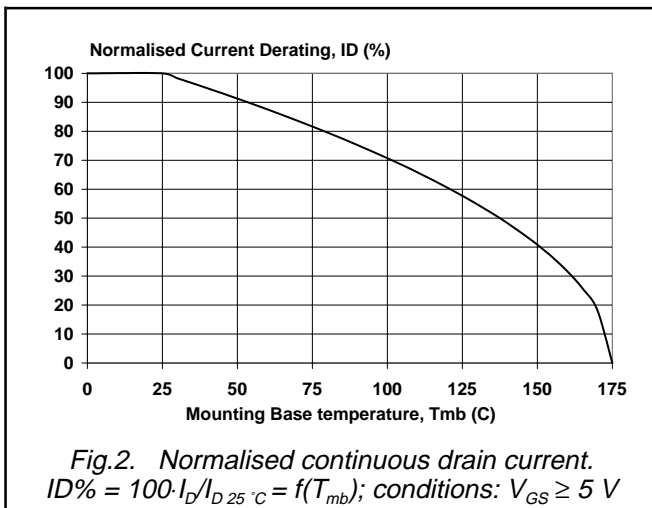
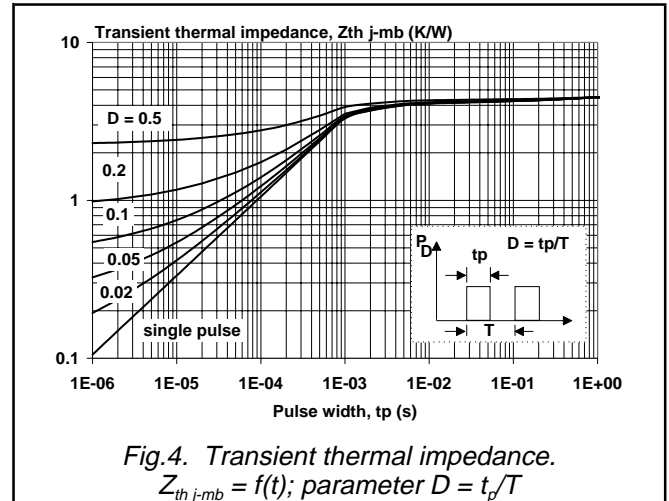
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**REVERSE DIODE LIMITING VALUES AND CHARACTERISTICS** $T_j = 25^\circ\text{C}$  unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$I_S$	Continuous source current (body diode)		-	-	10.3	A
$I_{SM}$	Pulsed source current (body diode)		-	-	41	A
$V_{SD}$	Diode forward voltage	$I_F = 10\text{ A}; V_{GS} = 0\text{ V}$	-	1.15	1.5	V
$t_{rr}$	Reverse recovery time	$I_F = 10\text{ A}; -di_F/dt = 100\text{ A}/\mu\text{s};$ $V_{GS} = 0\text{ V}; V_R = 30\text{ V}$	-	35	-	ns
$Q_{rr}$	Reverse recovery charge		-	55	-	nC

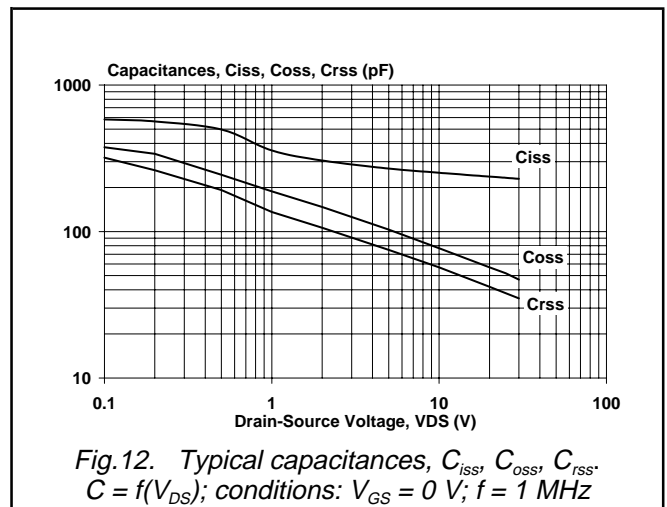
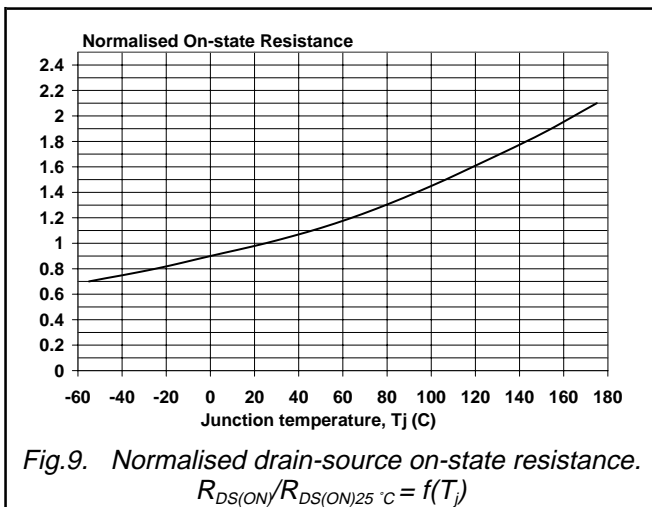
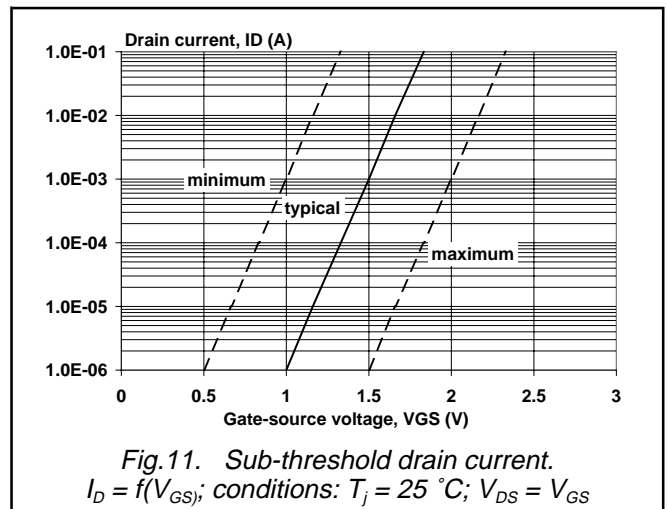
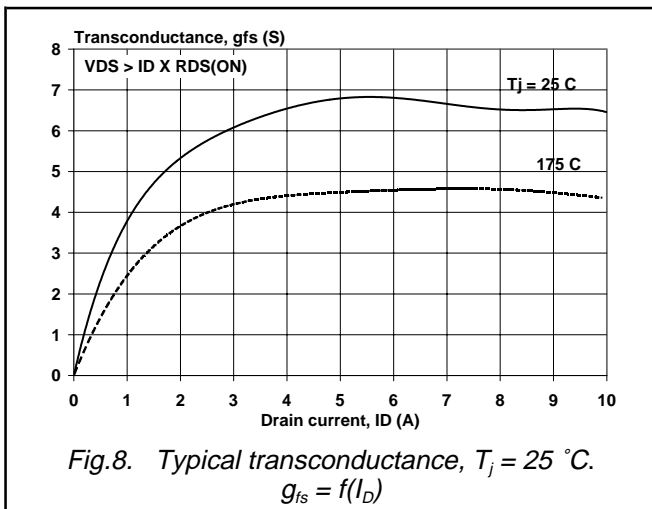
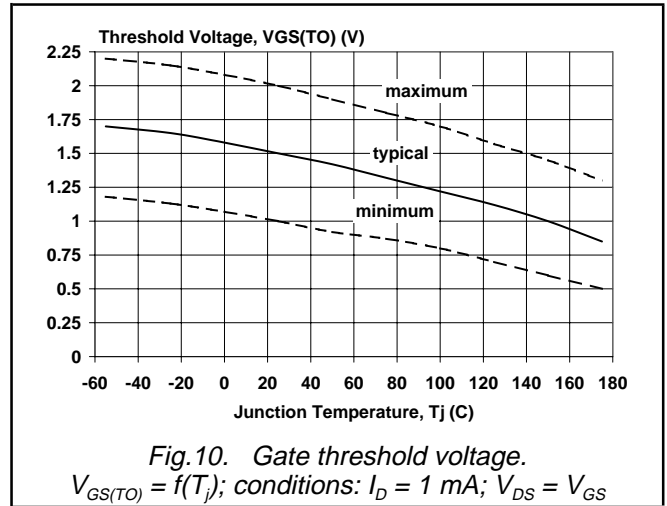
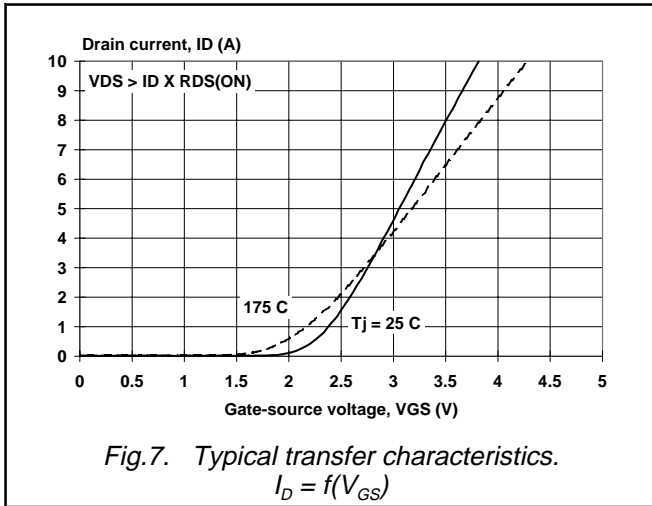
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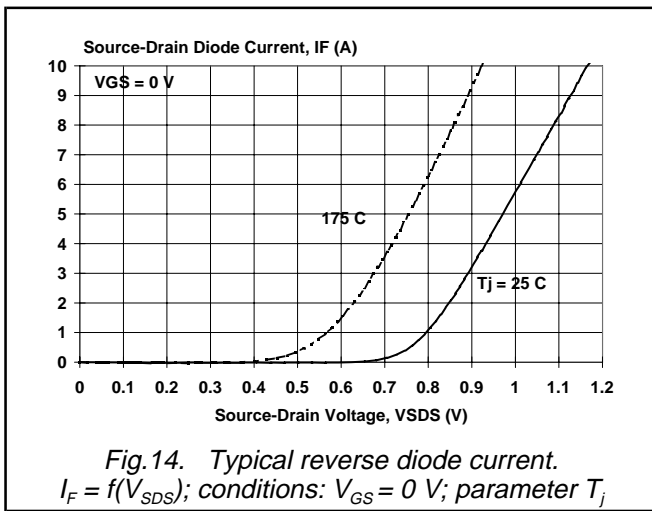
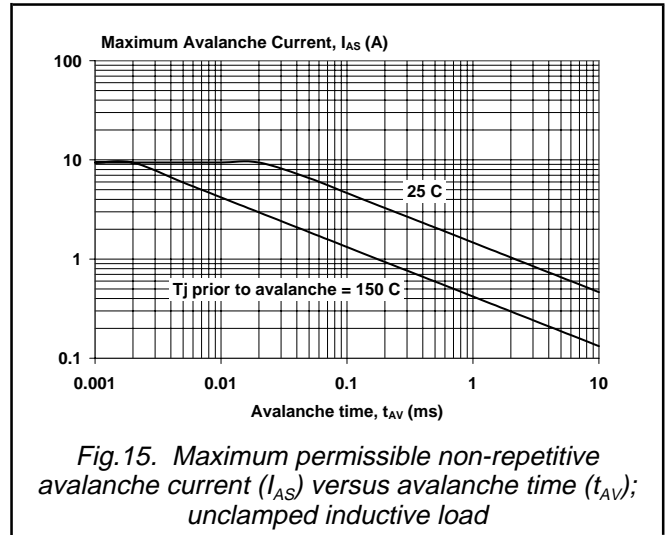
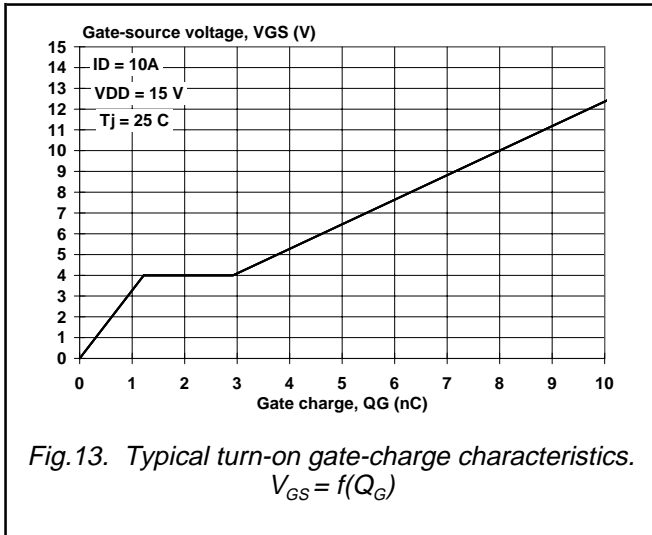
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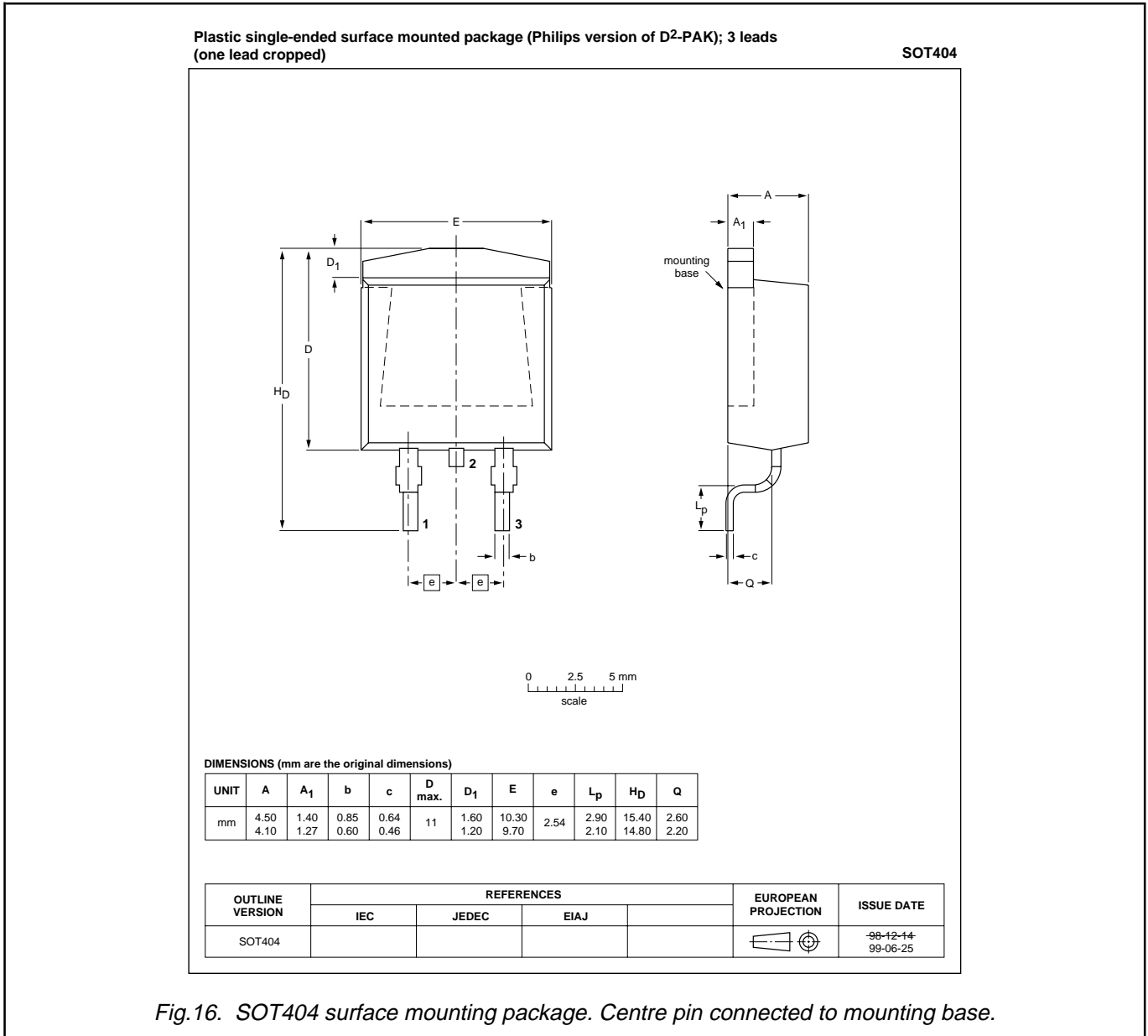
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MECHANICAL DATA



Notes

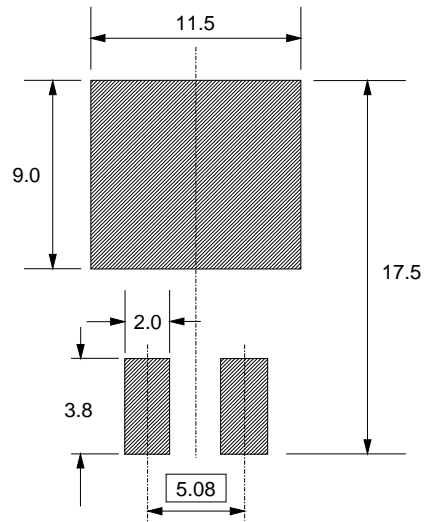
1. This product is supplied in anti-static packaging. The gate-source input must be protected against static discharge during transport or handling.
2. Refer to SMD Footprint Design and Soldering Guidelines, Data Handbook SC18.
3. Epoxy meets UL94 V0 at 1/8".

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**MOUNTING INSTRUCTIONS**

*Dimensions in mm*



*Fig.17. SOT404 : soldering pattern for surface mounting.*



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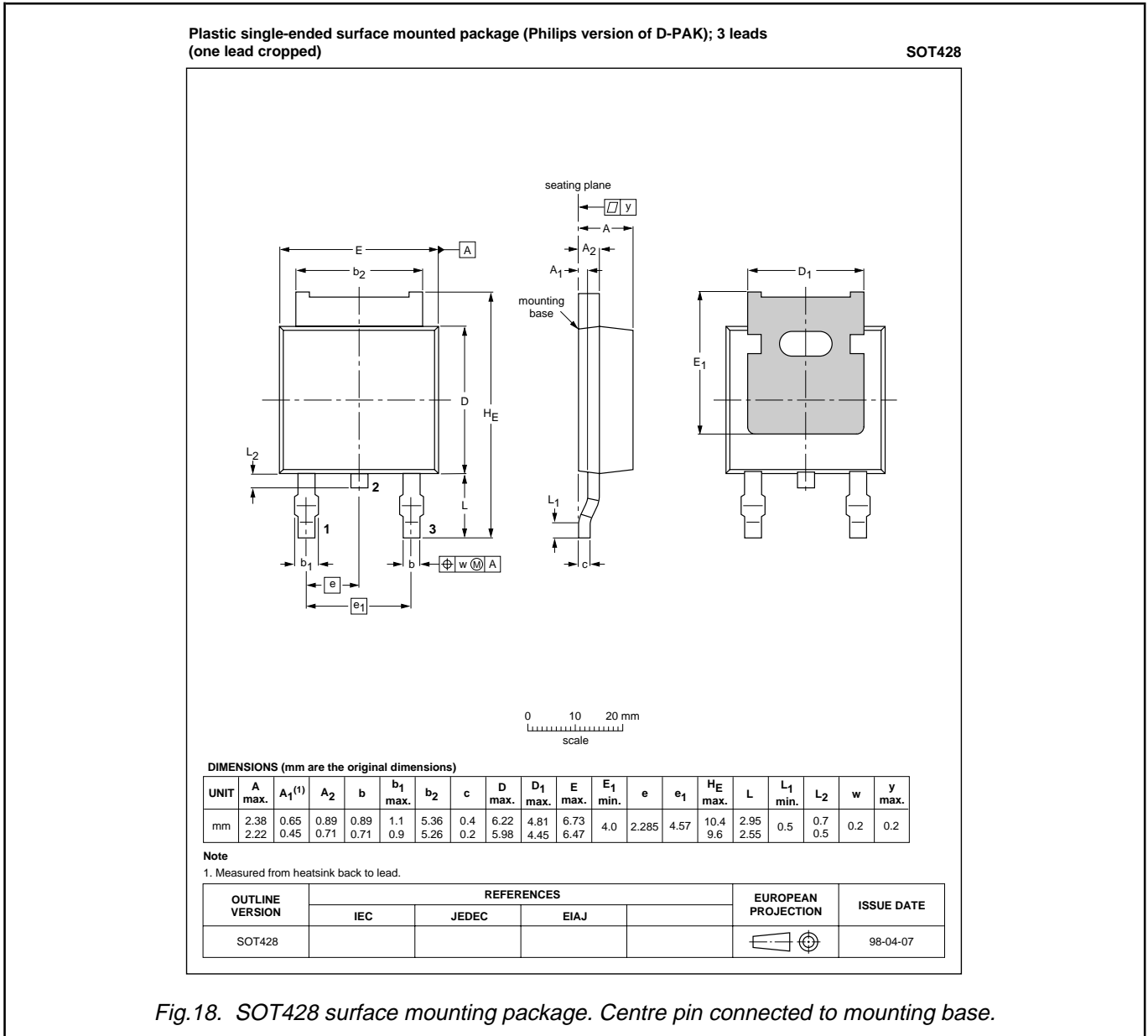


Fig.18. SOT428 surface mounting package. Centre pin connected to mounting base.

Notes

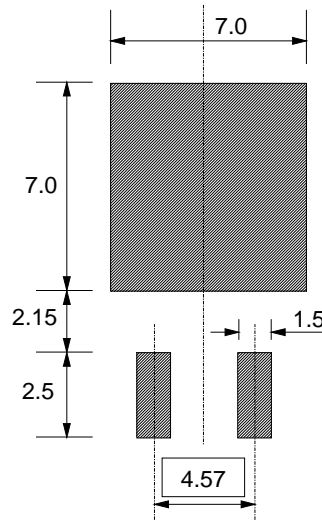
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**MOUNTING INSTRUCTIONS**

*Dimensions in mm*



*Fig.19. SOT428 : soldering pattern for surface mounting.*

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### DEFINITIONS

<b>Data sheet status</b>	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
<b>Limiting values</b>	
Limiting values are given in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of this specification is not implied. Exposure to limiting values for extended periods may affect device reliability.	
<b>Application information</b>	
Where application information is given, it is advisory and does not form part of the specification.	
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